

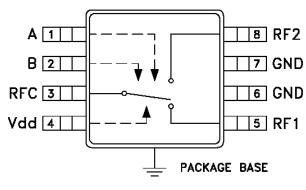


Typical Applications

The HMC5457MS8GE is ideal for:

- Cellular / 4G Infrastructure
- WiMAX, WiBro & Fixed Wireless
- Automotive Telematics
- Mobile Radio
- Test Equipment

Functional Diagram



HMC5457MS8GE

GaAs MMIC 10 WATT T/R SWITCH DC - 4 GHz

Features

Input P1dB: +40 dBm @ Vdd = +8V High Third Order Intercept: +62 dBm Positive Control: +3 to +10V Low Insertion Loss: 0.4 dB MSOP8G Package: 14.8 mm²

General Description

The HMC5457MS8GE is a high power SPDT switch in an 8-lead MSOPG package for use in transmit-receive applications which require very low distortion at high input signal power levels. The device can control signals from DC to 4 GHz. The design provides exceptional intermodulation performance; > +60 dBm third order intercept at +8V bias. RF1 and RF2 are reflective shorts when "OFF". On-chip circuitry allows single positive supply operation from +3 Vdc to +10 Vdc at very low DC current with control inputs compatible with CMOS logic families.

Electrical Specifications, $T_A = +25^{\circ}$ C, Vctl = 0/Vdd, Vdd = +8V (Unless Otherwise Stated), 50 Ohm System

| Paramete | r | Frequency | Min. | Тур. | Max. | Units |
|---|---|--|----------------|---------------------------------|---------------------------------|----------------------------|
| Insertion Loss | | DC - 1.0 GHz DC - 2.0 GHz DC - 2.5 GHz DC - 3.0 GHz DC - 4.0 GHz | | 0.4 0.6 0.8 0.9 1.3 | 0.6 0.8 1.1 1.3 2.0 | dB dB dB dB dB |
| Isolation | | DC - 4.0 GHz | 26 | 30 | | dB |
| Return Loss (On State) | DC - 1.0 GHz DC - 2.0 GHz DC - 3.0 GHz DC - 4.0 GHz | | | 35 30 20 10 | | dB dB dB dB |
| Input Power for 0.1dB Compression | Vdd = +3V Vdd = +5V Vdd = +8V | 0.1 - 4.0 GHz | | 32 37 38 | | dBm dBm dBm |
| Input Power for 1dB Compression | Vdd = +3V Vdd = +5V Vdd = +8V | 0.1 - 4.0 GHz | 32 35 38 | 35 38 41 | | dBm dBm dBm |
| Input Third Order Intercept (Two-tone input power = +30 dBm each tone) | 0.02 - 0.1 GHz 0.1 - 2.0 GHz 0.1 - 3.0 GHz 0.1 - 4.0 GHz | | | 47 64 63 63 | | dBm dBm dBm dBm |
| Switching Characteristics | | | | | | |
| | tRISE, tFALL (10/90% RF) tON, tOFF (50% CTL to 10/90% RF) | DC - 4.0 GHz | | 15 40 | | ns ns |

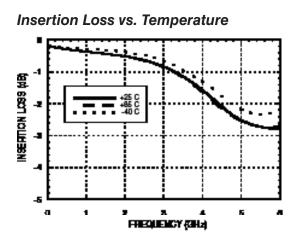
For price, delivery, and to place orders, please contact Hittite Microwave Corporation: 20 Alpha Road, Chelmsford, MA 01824 Phone: 978-250-3343 Fax: 978-250-3373 Order On-line at www.hittite.com



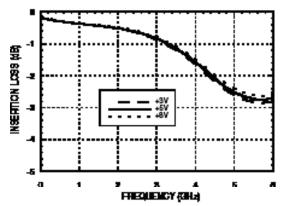


HMC5457MS8GE

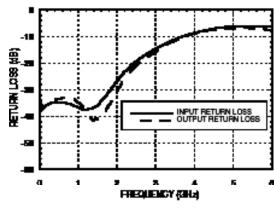
GaAs MMIC 10 WATT T/R SWITCH DC - 4 GHz

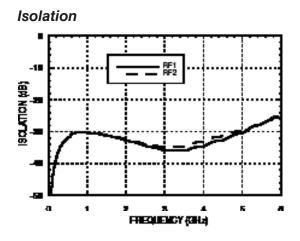


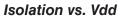
Insertion Loss vs. Vdd

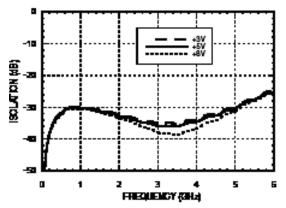


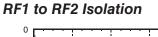


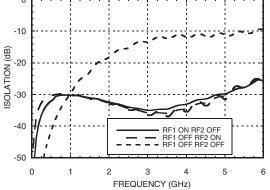








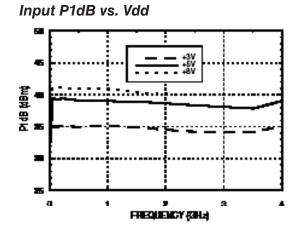




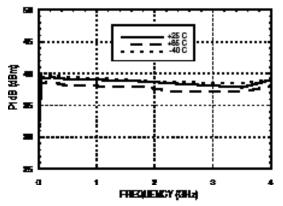




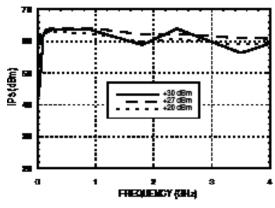
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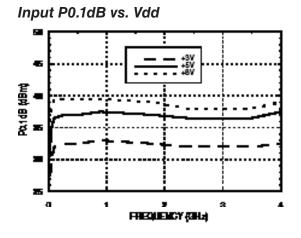


Input P1dB vs. Temperature @ Vdd = +5V

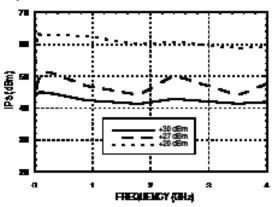


Input IP3 vs. Tone Power @ Vdd = +5V

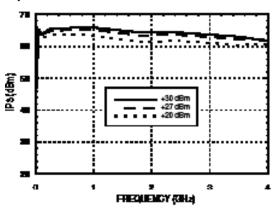




Input IP3 vs. Tone Power @ Vdd = +3V







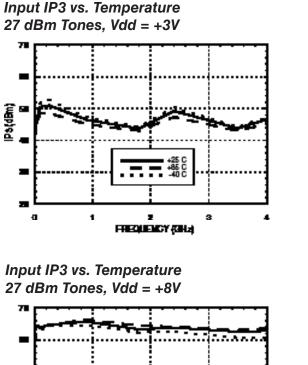
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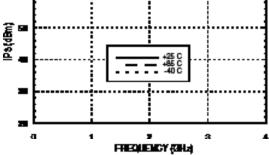




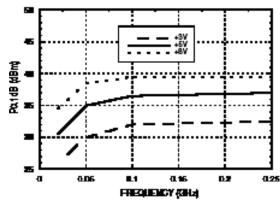
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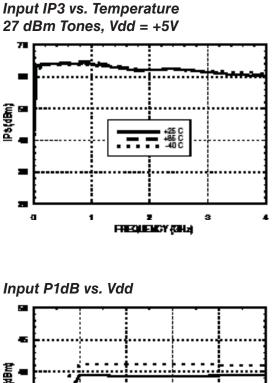
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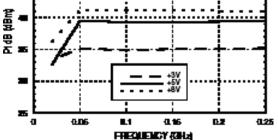




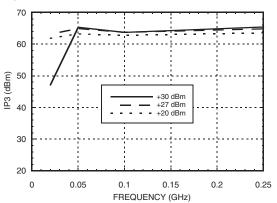
Input P0.1dB vs. Vdd







Input IP3 vs. Tone Power @ Vdd = +8V



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Bias Voltage & Current

| | Vdd (V) | Typical Idd (μA) | |
|----|---------|------------------|--|
| +3 | | 0.5 | |
| +5 | | 2 | |
| | +8 | 20 | |

Truth Table

| Control Input (Vctl) | | Signal Path State | |
|----------------------|------|-------------------|------------|
| А | В | RFC to RF1 | RFC to RF2 |
| High | Low | Off | On |
| Low | High | On | Off |
| Low | Low | Off | Off |

Absolute Maximum Ratings

| RF Input Power (Vdd = +8V, 50 Ohm source & load impedances) | +39 dBm (T = +85 °C) | |
|---|----------------------|--|
| Supply Voltage Range (Vdd) (Vctl = 0V) -0.2 to +12V | | |
| Control Voltage Range (A & B) | -0.2 to Vdd +0.5V | |
| Hot Switch Power Level (Vdd = +8V) | 39 dBm | |
| Channel Temperature | 150 °C | |
| Continuous Pdiss (T = 85 °C) (derate 25 mW/°C above 85 °C) 1.217 W | | |
| Thermal Resistance (Channel to ground paddle) | 53.4 °C/W | |
| Storage Temperature | -65 to +150 °C | |
| Operating Temperature -40 to +85 °C | | |
| ESD Rating | Class 1A HBM | |

Note: DC blocking capacitors are required at ports RFC, RF1 and RF2. Their value will determine the lowest transmission frequency.

Control Voltages & Currents

| State | Vdd = +3V (µA) | Vdd = +5V (µA) | Vdd = +8V (µA) |
|------------------|-------------------|-------------------|-------------------|
| Low (0 to +0.2V) | 0.5 | 2 | 20 |
| High (Vdd ±0.2V) | 0.1 | 0.1 | 0.1 |



ELECTROSTATIC SENSITIVE DEVICE OBSERVE HANDLING PRECAUTIONS

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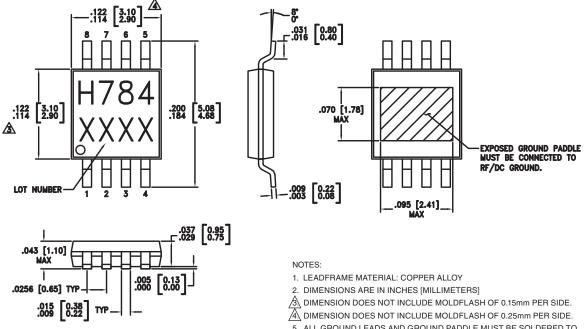


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Outline Drawing



5. ALL GROUND LEADS AND GROUND PADDLE MUST BE SOLDERED TO PCB RF GROUND.

Package Information

| [| Part Number | Package Body Material | Lead Finish | MSL Rating | Package Marking ^[1] |
|---|-------------|--|---------------|---------------------|--------------------------------|
| | HMC784MS8GE | RoHS-compliant Low Stress Injection Molded Plastic | 100% matte Sn | MSL1 ^[2] | <u>H784</u> XXXX |

[1] 4-Digit lot number XXXX

[2] Max peak reflow temperature of 260 $^\circ\text{C}$

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SWITCHES - SPDT - SMT

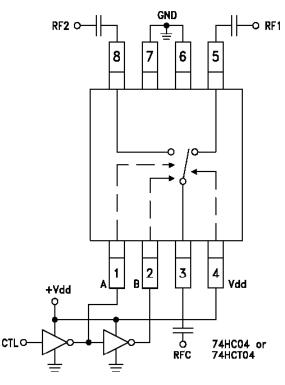




Pin Descriptions

| Pin Number | Function | Description | Interface Schematic |
|------------|---------------|---|---------------------|
| 1 | А | See truth table and control voltage table. | A,B 0 |
| 2 | В | See truth table and control voltage table. | ± c |
| 3, 5, 8 | RFC, RF1, RF2 | This pin is DC coupled and matched to 50 Ohms. Blocking capacitors are required. | |
| 4 | Vdd | Supply Voltage | |
| 6, 7 | GND | Package bottom must also be connected to PCB RF ground. | |

Typical Application Circuit



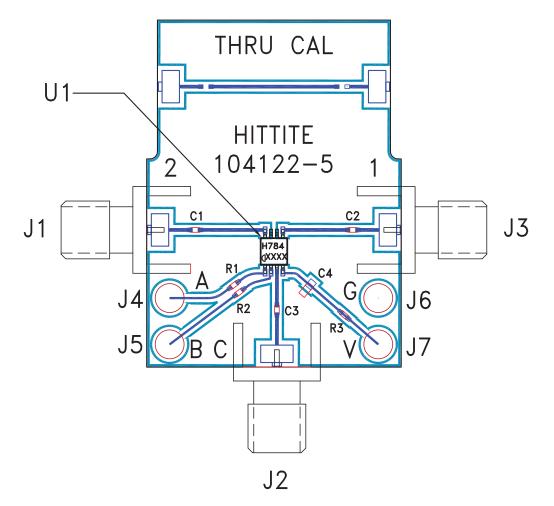
Notes:

- 1. Set logic gate and switch Vdd = +3V to +10V and use HCT series logic to provide a TTL driver interface.
- 2. Control inputs A/B can be driven directly with CMOS logic (HC) with Vdd of +3 to +10 Volts applied to the CMOS logic gates and to pin 4 of the RF switch.
- 3. DC Blocking capacitors are required for each RF port as shown. Capacitor value determines lowest frequency of operation.
- 4. Highest RF signal power capability is achieved with V set to +10V. The switch will operate properly (but at lower RF power capability) at bias voltages down to +3V.





Evaluation Circuit Board



List of Materials for Evaluation PCB 104124 [1]

| Item | Description | |
|---------|-----------------------------|--|
| J1 - J3 | PCB Mount SMA RF Connector | |
| J4 - J7 | DC Pin | |
| C1 - C3 | 100 pF capacitor, 0402 Pkg. | |
| C4 | 10 KpF capacitor, 0603 Pkg. | |
| R1 - R3 | 100 Ohm Resistor, 0402 Pkg. | |
| U1 | HMC5457MS8GE T/R Switch | |
| PCB [2] | 104122 Evaluation PCB | |

Reference this number when ordering complete evaluation PCB
Circuit Board Material: Rogers 4350

The circuit board used in the final application should be generated with proper RF circuit design techniques. Signal lines at the RF port should have 50 ohm impedance and the package ground leads and package bottom should be connected directly to the ground plane similar to that shown above. The evaluation circuit board shown above is available from Hittite Microwave Corporation upon request.